

Used in Lieu of PTO/SB/08A/B
(Based on PTO 11-07 version)

Substitute for form 1449/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(Use as many sheets as necessary)</i>				Complete if Known	
				Application Number	10/774,890-Conf. #8754
				Filing Date	February 9, 2004
				First Named Inventor	Eugene A. Fitzgerald
				Art Unit	2818
				Examiner Name	D. A. Le
Sheet	1	of	2	Attorney Docket Number	ASC-049C1

ALL REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /Die/ (05/27/2008)

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
	A354*	US-4,994,866	02-19-1991	Awano et al.	
	A355*	US-5,849,612	12-15-1998	Takahashi et al.	
	A356*	US-6,008,128	12-28-1999	Habuka et al.	
	A357*	US-6,593,625-A1	07-15-2003	Christiansen et al.	
	A358*	US-6,689,211	02-10-2004	Wu et al.	
	A359*	US-6,723,621	04-20-2004	Cardone et al.	
	A360*	US-6,727,550-A1	04-27-2004	Tezuka et al.	
	A361*	US-6,858,502-A1	02-22-2005	Chu et al.	
	A362*	US-6,879,053	04-12-2005	Welches et al.	
	A363*	US-6,881,632-A1	04-19-2005	Fitzgerald et al.	
	A364*	US-2002/0079427	06-27-2002	Xu et al.	
	A364*	US-6,444,578	09-03-2002	Cabral et al.	

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	Foreign Patent Document Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages Or Relevant Figures Appear	T ⁶

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. * CITE NO.: Those application(s) which are marked with an single asterisk (*) next to the Cite No. are not supplied (under 37 CFR 1.98(a)(2)(iii)) because that application was filed after June 30, 2003 or is available in the IFW. ¹ Applicant's unique citation designation number (optional). ² See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

NON PATENT LITERATURE DOCUMENTS					
Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²		
	C342	AmberWave Systems Corporation's Responses to Intel's Sixth Set of Interrogatories, C.A. No. 05-301-KAJ (consolidated) (September 5, 2006)			
	C343	AmberWave Systems Corporation's Responses to Intel's Fifth Set of Requests for Production, Civil Action No. 05-301-KAJ (consolidated) (June 30, 2006)			
	C344	AmberWave Systems Corporation's Responses to Intel's Fifth Set of Interrogatories, C.A. No. 05-301-KAJ (consolidated) (June 19, 2006)			
	C345	AmberWave Systems Corporation's Responses to Intel's Third Set of Requests for Production, C.A. No. 05-301-KAJ (consolidated) (February 10, 2006)			
	C346	AmberWave Systems Corporation's First Supplemental Responses to Intel's First Set of Interrogatories, C.A. No. 05-837-KAJ (July 12, 2006)			
	C347	Bera et al., "Gas Source Molecular Beam Epitaxy Grown Strained-Si Films on Step-Graded Relaxed Si _{1-x} Ge _x for MOS Applications," 28 J. Electron. Mat. 2, pp. 98-104 (1999).			

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Examiner Signature	/Dung A. Le/ (05/27/2008)	Date Considered	
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	C348	Corrected Request for Inter Partes Reexamination of U.S. Patent No 6,649,480, January 12, 2007.	
	C349	Intel's Amended and Supplemented Responses and Objections to AmberWave's First Set of Interrogatories, Civil Action No. 05-301-KAJ (August 7, 2006)	
	C350	Intel's Responses and Objections to AmberWave's First Set of Requests for Production, Civil Action No. 05-837-KAJ (February 3, 2006)	
	C351	Intel's Amended Responses and Objections to AmberWave's First Set of Interrogatories, Civil Action No. 05-837-KAJ (February 3, 2006).	
	C352	Intel's Responses and Objections to AmberWave's First Set of Interrogatories, Civil Action No. 05-837-KAJ (February 3, 2006)	
	C353	International Search Report for International Patent Application No PCT/US01/46322, mailed 1/22/2003.	
	C354	John et. al., "Strained Si n-channel metal-oxide-semiconductor transistor on relaxed Si _{1-x} Ge _x formed by Ion Implantation of Ge," 74 Applied Physics Letters 14, pp. 2076-78 (1999).	
	C355	Office action in Inter Partes Reexamination of U.S. Patent No. 6,649,480, March 23, 2007.	
	C356	Request for Inter Partes Reexamination of U.S. Patent No. 6,649,480, October 24, 2006.	
	C357	Wolf and Tauber, Silicon Processing for the VLSI Era Volume 1: Process Technology, Lattice Press, Sunset Beach, CA, 1986, pp. 124-160.	

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